L Number	Hits	Search Text	DB	Time stamp
	7	(substrate same (insulating or insulator or dielectric) same lectrode same (black near	USPAT; US-PGPUB;	2003/01/26 12:40
		(matrix r matrices)) same transparent same protrusi n)	EPO; JP ; DERWENT; IBM_TDB	
•	8	(substrate same (insulating or insulator or	USPAT;	2003/01/26
ł		dielectric) same (black near (matrix or	US-PGPUB;	12:41
		matrices)) same transparent same	EPO; JPO;	
		protrusion)	DERWENT; IBM_TDB	
	3	(substrate same (insulating or insulator or	USPAT;	2003/01/26
		dielectric) same (black near (matrix or	US-PGPUB;	12:42
		matrices)) same transparent same	EPO; JPO;	
		protrusion) and organic	DERWENT;	
			IBM_TDB	
	8522	(black near (matrix or matrices))	USPAT;	2003/01/26
			US-PGPUB;	12:42
			EPO; JPO;	
			DERWENT;	
	4240		IBM_TDB	
	4513	((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transparent	US-PGPUB;	12:42
			EPO; JPO;	
			DERWENT;	
	2902	///blook noor (motive or motive or)	IBM_TDB	000015 1:55
	2302	(((black near (matrix or matrices))) and transparent) and pixel	USPAT;	2003/01/26
		nansparent, and pixel	US-PGPUB;	12:42
		A	EPO; JPO;	
	A		DERWENT; IBM_TDB	
	2729	((((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate	US-PGPUB:	12:43
		, and piner, and substitute	EPO; JPO;	12.73
			DERWENT;	
			IBM_TDB	
	1228	(((((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and	US-PGPUB;	12:43
		organic	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	114	((((((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and	US-PGPUB;	12:43
		organic) and protrusion	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	111	(((((((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transpar nt) and pix l) and substrate) and	US-PGPUB;	12:43
		rganic) and pr trusi n) and c I r	EPO; JPO;	
			DERWENT;	
	į		IBM_TDB	

•	106	((((((((black n ar (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and	US-PGPUB;	12:44
		rganic) and protrusi n) and c l r) and	EPO; JPO;	
		lectr d	DERWENT;	
			IBM_TDB	
-	28	((((((((black n ar (matrix r matric s))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and	US-PGPUB;	12:44
		organic) and protrusion) and color) and	EPO; JPO;	
		electrode) and (black near (matrix or	DERWENT;	
		matrices)).ti,ab,clm.	IBM_TDB	

L Number	Hits	Search T xt	DB	Tim stamp
	2731	(transpar nt n ar electrod) n ar10	USPAT;	2003/01/27
		(insulating rinsulat r r dielectric) near10	US-PGPUB;	09:35
		substrat	EPO; JPO;	
			DERWENT;	
	2	//transporent near alectuada)	IBM_TDB	0000/04/07
		((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:37
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) near5 (transparent near	DERWENT;	
	4	electrode) near5 protrusion)	IBM_TDB	0000/04/07
	4	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:40
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) near10 (transparent near	DERWENT;	
	4	electrode) near10 protrusion)	IBM_TDB	
	4	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:41
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) near20 (transparent near	DERWENT;	
		electrode) near20 protrusion)	IBM_TDB	
	3	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:42
		substrate) and ((black near (matrix or	EPO; JPO;	
1		matrices)) same (transparent near	DERWENT;	
		electrode) same protrusion).ti,ab,clm.	IBM_TDB	
***************************************	3	((transparent near electrode) near10	USPAT;	2003/01/27
	1	(insulating or insulator or dielectric) near10	US-PGPUB;	09:42
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) same (transparent near2	DERWENT;	
	_ [electrode) same protrusion).ti,ab,clm.	IBM_TDB	
	3	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:43
	1 7 1	substrate) and ((black near (matrix or	EPO; JPO;	
Į,		matrices)) same (transparent near3	DERWENT;	
		electrode) same protrusion).ti,ab,clm.	IBM_TDB	
	4	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:43
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) same (transparent near3	DERWENT;	
		electrode) same protrusion)	IBM_TDB	
	10	((black near (matrix or matrices)) same	USPAT;	2003/01/27
		(transparent near3 electrode) same	US-PGPUB;	09:45
		protrusion)	EPO; JPO;	
			DERWENT;	· .
			IBM_TDB	
	1	(((black near (matrix 'r matric s)) sam	USPAT;	2003/01/27
		(transpar nt n ar3 ctr d) sam	US-PGPUB;	09:45
		pr trusi n)) and organic	EPO; JPO;	_
		-	DERWENT;	
			IBM_TDB	

-	6	(((black n ar (matrix r matric s)) sam (transpar nt near3 l ctr d) sam protrusion)) and pix l	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/27 09:45	
			IBM TDB		

130	(US-6504592-\$ r US-6476890-\$ r	USPAT;	2003/01/27
	US-6476898-\$ r US-6437847-\$ or	US-PGPUB;	09:51
	US-6441873-\$ r US-6476882-\$ or	JPO;	
	US-6392728-\$ r US-6323594-\$ r	DERWENT	
	US-6266121-\$ r US-6215243-\$ or		
	US-6239856-\$ or US-6208394-\$ r		
	US-6175395-\$ or US-6163358-\$ or		_
	US-6091472-\$ or US-6069674-\$ or		
	US-6008877-\$ or US-5995190-\$ or		
	US-5999236-\$ or US-5946062-\$ or		
	US-5754267-\$ or US-5805249-\$ or		
	US-5815224-\$ or US-5729317-\$ or		
	US-5742371-\$ or US-5640216-\$).did. or		
	(US-5654781-\$ or US-5477351-\$ or		
	US-6433852-\$ or US-6504591-\$ or		
	US-6351078-\$ or US-6498592-\$ or		
	US-6239470-\$ or US-6262784-\$ or		
	US-6243146-\$ or US-6114715-\$ or		
	US-6198520-\$ or US-6162510-\$ or		
	US-6040887-\$ or US-6057896-\$ or		
	US-5870160-\$ or US-5943107-\$ or		
	US-6034747-\$ or US-5478611-\$ or		
	US-5815226-\$ or US-5739880-\$ or		
	US-5721076-\$ or US-6424402-\$ or		
	US-6169293-\$ or US-6275280-\$ or		
	US-5982471-\$ or US-6066448-\$ or		
	US-5952708-\$).did. or (US-5843332-\$ or		
111 - 12	US-5558927-\$ or US-5619097-\$ or		
	US-6266117-\$ or US-6300152-\$ or		
	US-6509939-\$ or US-6429916-\$ or	1	
	US-6429917-\$ or US-6476783-\$ or		
	US-6411360-\$ or US-6296750-\$ or		
	US-6373540-\$ or US-6392729-\$ or		
	US-6407782-\$ or US-6356330-\$ or		
	US-6281957-\$ or US-6221543-\$ or		
	US-6224730-\$ or US-6208404-\$ or		
İ	US-6162654-\$ or US-6157426-\$ or		
	US-6068750-\$ or US-6117294-\$ or		Į.
	US-6118506-\$ or US-6122025-\$ or		
	US-6005651-\$ or US-5956109-\$).did. or		
	(US-5754263-\$ or US-5781254-\$ or		
	US-5689318-\$ or US-5691788-\$ or		
	US-5703668-\$ or US-5633739-\$ or		
	US-5631753-\$ or US-5299041-\$ or		
	US-5495354-\$ or US-5619357-\$ or		1
	US-5626796-\$ or US-6388722-\$ or	•	
	US-6404480-\$ or US-6429059-\$ or	I	
İ	US-6433842-\$ r US-6489720-\$ or		
	US-6013930-\$ r US-6121660-\$ r		
	US-6124604-\$ r US-6177974-\$ r		
	US-6204535-\$ or US-6219113-\$ r		
	US-6281952-\$ r US-5529524-\$ or		
	US-5548181-\$ or US-5587623-\$ r		
	US-5847792-\$).did. or (US-6327016-\$).did. o		
arch Hist ry 2/9/03	፲ዚ38:2¢040 04 9656-\$ or US-20010013913-\$ or		
1 -	e !/69303220056958-\$)spid. r	1	1

	1	((US-6504592-\$ r US-6476890-\$ r	USPAT;	2003/01/27
ļ		US-6476898-\$ r US-6437847-\$ r	US-PGPUB;	09:56
		US-6441873-\$ or US-6476882-\$ r	EPO; JP ;	
		US-6392728-\$ or US-6323594-\$ or	DERWENT;	
		US-6266121-\$ or US-6215243-\$ r	IBM_TDB	
		US-6239856-\$ or US-6208394-\$ r		
		US-6175395-\$ or US-6163358-\$ or	141	
		US-6091472-\$ or US-6069674-\$ or	·	
		US-6008877-\$ or US-5995190-\$ or	\$	
		US-5999236-\$ or US-5946062-\$ or		
		US-5754267-\$ or US-5805249-\$ or		
		US-5815224-\$ or US-5729317-\$ or		
		US-5742371-\$ or US-5640216-\$).did. or		
		(US-5654781-\$ or US-5477351-\$ or	P	
		US-6433852-\$ or US-6504591-\$ or		
		US-6351078-\$ or US-6498592-\$ or		
		US-6239470-\$ or US-6262784-\$ or		
		US-6243146-\$ or US-6114715-\$ or		
		US-6198520-\$ or US-6162510-\$ or	11	1 4
\		US-6040887-\$ or US-6057896-\$ or	11	
		US-5870160-\$ or US-5943107-\$ or		
		US-6034747-\$ or US-5478611-\$ or		1
		US-5815226-\$ or US-5739880-\$ or		
		US-5721076-\$ or US-6424402-\$ or		
		US-6169293-\$ or US-6275280-\$ or		
		US-5982471-\$ or US-6066448-\$ or		
		US-5952708-\$).did. or (US-5843332-\$ or		
		US-5558927-\$ or US-5619097-\$ or		
		US-6266117-\$ or US-6300152-\$ or		
		US-6509939-\$ or US-6429916-\$ or		
		US-6429917-\$ or US-6476783-\$ or		
		US-6411360-\$ or US-6296750-\$ or		
		US-6373540-\$ or US-6392729-\$ or		
		US-6407782-\$ or US-6356330-\$ or		
ì		US-6281957-\$ or US-6221543-\$ or		
		US-6224730-\$ or US-6208404-\$ or		
		US-6162654-\$ or US-6157426-\$ or		
		US-6068750-\$ or US-6117294-\$ or		
		US-6118506-\$ or US-6122025-\$ or		
		US-6005651-\$ or US-5956109-\$).did. or		
		(US-5754263-\$ or US-5781254-\$ or		
		US-5689318-\$ or US-5691788-\$ or		
		US-5703668-\$ or US-5633739-\$ or		
		US-5631753-\$ or US-5299041-\$ or		
		US-5495354-\$ or US-5619357-\$ or		
		US-5626796-\$ or US-6388722-\$ or		
		US-6404480-\$ or US-6429059-\$ or		
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-	1	(((insulating rinsulator or diel ctric) sam	USPAT;	2003/01/27
		substrat) and (transparent n ar electr d)	US-P PUB;	09:56
		and (bla k near (matrix or matrices)) and	EPO; JPO;	
		pr trusion and (col r near filter) and rganic	DERWENT;	
		and (photosensitive) and (lith grahpy r	IBM_TDB	
		ph tolith graphy) and pix l).ti,ab,clm.	_	
	1	(((insulating or insulator or dielectric) same	USPAT;	2003/01/27
_	•	substrate) and (transparent near electrode)	US-PGPUB;	09:57
		and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and (photosensitive) and pixel).ti,ab,clm.	IBM_TDB	
	1	(((insulating or insulator or dielectric) same	USPAT;	2003/01/27
1		,,,	US-PGPUB;	09:57
		substrate) and (transparent near electrode)		09.97
		and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and pixel).ti,ab,clm.	IBM_TDB	0000/04/07
-	36	(((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate) and (transparent near electrode)	US-PGPUB;	09:58
		and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and pixel)	IBM_TDB	
-	28096	((((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate) and (transparent near electrode)	US-PGPUB;	10:00
		and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and pixel)) amd (black near (matrix or	IBM_TDB	·
		matrices)).ti,ab,clm.		
	10	((((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate) and (transparent near electrode)	US-PGPUB;	10:00
		and (black near (matrix or matrices)) and	EPO; JPO;	
	ŧ	protrusion and (color near filter) and organic	DERWENT;	
		and pixel)) and (black near (matrix or	IBM_TDB	
		matrices)).ti,ab,clm.	_	
_	9	(((((insulating or insulator or dielectric)	USPAT;	2003/01/27
_		same substrate) and (transparent near	US-PGPUB;	10:01
		electrode) and (black near (matrix or	EPO; JPO;	10.01
		matrices)) and protrusion and (color near	DERWENT;	
		filter) and organic and pixel)) and (black	1	
		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	
		near (matrix or matrices)).ti,ab,clm.) and		
		substrate.ti,ab,clm.	HEDAT	2002/04/27
•	8	((((((insulating or insulator or dielectric)	USPAT;	2003/01/27
		same substrate) and (transparent near	US-PGPUB;	10:01
		electrode) and (black near (matrix or	EPO; JPO;	
		matrices)) and protrusion and (color near	DERWENT;	
		filter) and organic and pixel)) and (black	IBM_TDB	
		near (matrix or matrices)).ti,ab,clm.) and	i 11	
		substrate.ti,ab,clm.) and		
		transpar nt.ti,ab,clm.		

-	5	((((((((insulating r insulator r diel ctri) sam substrat) and (transparent near lectrod) and (black near (matrix r matrices)) and protrusion and (col r n ar filter) and rganic and pixel)) and (black near (matrix or matric s)).ti,ab,clm.) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 10:02
	4	substrate.ti,ab,clm.) and transparent.ti,ab,clm.) and data (((((((((insulating or insulator or dielectric) same substrate) and (transparent near electrode) and (black near (matrix or	USPAT; US-PGPUB; EPO; JPO;	2003/01/27 11:12
		matrices)) and protrusion and (color near filter) and organic and pixel)) and (black near (matrix or matrices)).ti,ab,clm.) and substrate.ti,ab,clm.) and transparent.ti,ab,clm.) and data) and gate	DERWENT; IBM_TDB	
	1	(black near matrix) and chrome and (color near filter) and (gate near line) and (data near line) and (pixel near electrode) and (redundant near data)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 11:14
-	3	(black near matrix) and (color near filter) and (gate near line) and (data near line) and (pixel near electrode) and (redundant near data)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 11:18
	3559	(transparent near2 electrode near3 (insulating or insulator or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 11:20
	17	((transparent near2 electrode near3 (insulating or insulator or dielectric))) and ((light near (block or blocking or blocked)) near5 metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 11:23
-	7	(((transparent near2 electrode near3 (insulating or insulator or dielectric))) and ((light near (block or blocking or blocked)) near5 metal)) and ((light near (block or blocking or blocked)) near5 metal near10 transparent)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 11:24
	1	((((transparent near2 electrode near3 (insulating or insulator or dielectric))) and ((light near (block or blocking or blocked)) near5 metal)) and ((light near (block or blocking or blocked)) near5 metal near10 transpar nt)) and (protrusi n\$10 near5 organic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 11:24

_	1	((((transpar nt n ar2 ele tr de n ar3	USPAT;	2003/01/27
		(insulating rinsulat r r di l ctric))) and	US-P PUB;	11:25
		((light near (block or bl cking or bl ck d))	EPO; JPO;	
	. 13	near5 metal)) and ((light n ar (block or	DERWENT;	
		blocking r block d)) n ar5 m tal near10	IBM_TDB	
1		transparent)) and (pr trusi n\$10 sam	_	
		organic)		
_	2	((((transparent near2 electrode near3	USPAT;	2003/01/27
	_	(insulating or insulator or dielectric))) and	US-PGPUB;	11:25
		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)) and ((light near (block or	DERWENT;	
		blocking or blocked)) near5 metal near10	IBM_TDB	
		transparent)) and (protrusion\$10 and	_	
		organic)		
	2	(((((transparent near2 electrode near3	USPAT;	2003/01/27
	_	(insulating or insulator or dielectric))) and	US-PGPUB;	11:26
		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)) and ((light near (block or	DERWENT;	
	!	blocking or blocked)) near5 metal near10	IBM_TDB	
		transparent)) and (protrusion\$10 and		
		organic)) and photosensitive		
_	2	((((((transparent near2 electrode near3	USPAT;	2003/01/27
	_	(insulating or insulator or dielectric))) and	US-PGPUB;	11:26
1 1 1		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)) and ((light near (block or	DERWENT;	
		blocking or blocked)) near5 metal near10	IBM_TDB	
		transparent)) and (protrusion\$10 and		
	1 1	organic)) and photosensitive) and pixel		11 1
_	2	((((((transparent near2 electrode near3	USPAT;	2003/01/27
	1 2	(insulating or insulator or dielectric))) and	US-PGPUB;	11:26
		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)) and ((light near (block or	DERWENT;	
		blocking or blocked)) near5 metal near10	IBM_TDB	
		transparent)) and (protrusion\$10 and		
		organic)) and photosensitive) and pixel) and		
	1	(black near (matrix or matrices))		İ
-	2	((((((((transparent near2 electrode near3	USPAT;	2003/01/27
	_	(insulating or insulator or dielectric))) and	US-PGPUB;	11:28
		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)) and ((light near (block or	DERWENT;	
		blocking or blocked)) near5 metal near10	IBM_TDB	
		transparent)) and (protrusion\$10 and		
		organic)) and photosensitive) and pixel) and		
		(black near (matrix or matrices))) and		
		(transparent near electrode)		

•	2	((((((((transparent near2 electr d n ar3	USPAT;	2003/01/27
		(insulating or insulator or diel ctric))) and ((light near (bl ck or bl cking r blo k d)) n ar5 metal)) and ((light n ar (block or	US-PGPUB; EPO; JPO; DERWENT;	11:28
		blocking r blocked)) n ar5 metal near10 transpar nt)) and (protrusi n\$10 and	IBM_TDB	
		organic)) and photosensitive) and pixel) and (black near (matrix or matrices))) and (transparent near electrode)) and (black		
		near (matrix or matrices))		
	2	((((((((((((((((((((((((((((((((((((((USPAT; US-PGPUB;	2003/01/27 12:15
		((light near (block or blocking or blocked)) near5 metal)) and ((light near (block or	EPO; JPO; DERWENT;	
		blocking or blocked)) near5 metal near10	IBM_TDB	
		transparent)) and (protrusion\$10 and organic)) and photosensitive) and pixel) and		
		(black near (matrix or matrices))) and		
,		(transparent near electrode)) and (black		
	<u>.</u>	near (matrix or matrices))) and (mask or lithograp\$7 or photolithograp\$7 or photo-litho\$7)		
	0	((((((((((((((((((((((((((((((((((((((USPAT; US-PGPUB;	2003/01/27 12:16
		(insulating or insulator or dielectric))) and ((light near (block or blocking or blocked))	EPO; JPO;	12.10
		near5 metal)) and ((light near (block or	DERWENT;	
		blocking or blocked)) near5 metal near10 transparent)) and (protrusion\$10 and	IBM_TDB	
		organic)) and photosensitive) and pixel) and		
		(black near (matrix or matrices))) and		
		(transparent near electrode)) and (black near (matrix or matrices))) and (mask or		
		lithograp\$7 or photolithograp\$7 or		
		photo-litho\$7)) and (qbetech or "qbe tech" or "qbe technologies" or "aqcess	i c	
	2	technologies") qbetech or "qbe tech" or "qbe technologies"	USPAT;	2003/01/27
		or "aqcess technologies"	US-PGPUB;	12:44
			EPO; JPO; DERWENT;	
			IBM_TDB	
	449	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator)).clm.	US-PGPUB; EPO; JPO;	12:44
	į.		DERWENT;	
_ ' .	648	((transparent near electrode) near10	IBM_TDB USPAT;	2003/01/27
-	0-10	(insulating or insulator or di ctric)).clm.	US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT; IBM_TDB	

•	2	(((transparent n ar electrod) n ar10	USPAT;	2003/01/27
		(insulating or insulator or di ctric)) sam	US-PGPUB;	12:46
		(black n ar (matrix or matrices)) same	EPO; JPO;	
		protrusi n).clm.	DERWENT;	
			IBM_TDB	
	2	((((transparent n ar electrod) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric)) same	US-PGPUB;	12:47
		(black near (matrix or matrices)) same	EPO; JPO;	
İ		protrusion).clm.) and photosensitive	DERWENT;	
			IBM_TDB	
	2	(((((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric)) same	US-PGPUB;	12:48
		(black near (matrix or matrices)) same	EPO; JPO;	
	A	protrusion).clm.) and photosensitive) and	DERWENT;	
		(color near filter)	IBM_TDB	
	1	((((((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric)) same	US-PGPUB;	12:48
		(black near (matrix or matrices)) same	EPO; JPO;	
		protrusion).clm.) and photosensitive) and	DERWENT;	
		(color near filter)) and (method or	IBM_TDB	
		process).clm.		
	2	((transparent near electrode) and (black	USPAT;	2003/01/27
		near (matrix or matrices)) and	US-PGPUB;	12:58
		(photosensitive) and (etch or etching or	EPO; JPO;	
		etched) and mask and (method or	DERWENT;	
İ		process)).clm.	IBM_TDB	
	6	((transparent near electrode) and (black	USPAT;	2003/01/27
		near (matrix or matrices)) and (etch or	US-PGPUB;	12:52
		etching or etched) and mask and (method or	EPO; JPO;	
		process)).clm.	DERWENT;	
ĺ		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	IBM_TDB	
	3	(((transparent near electrode) and (black	USPAT;	2003/01/27
	1	near (matrix or matrices)) and (etch or	US-PGPUB;	12:51
		etching or etched) and mask and (method or	EPO; JPO;	
1		process)).clm.) and photosensitive	DERWENT;	
		F • • • • • • • • • • • • • • • • • • •	IBM_TDB	
	17	((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matrices)) and (etch or etching or etched)	US-PGPUB;	12:52
		and mask and (method or process)).clm.	EPO; JPO;	
		and made and (modern process),	DERWENT;	
			IBM_TDB	
	4	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
	7	matrices)) and (etch or etching or etched)	US-PGPUB;	12:52
		and mask and (method or process)).clm.)	EPO; JPO;	
		and photosensitive.clm.	DERWENT;	
		and photosensitivelenin	IBM_TDB	
	5	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
	3	matric s)) and (et h or etching retched)	US-PGPUB;	12:53
		and mask and (m thod or proc ss)).clm.)	EPO; JPO;	
			DERWENT;	
		and ph t s nsitiv	IBM_TDB	

•	23486	ph t sensitiv .clm.	USPAT;	2003/01/27
			US-PGPUB;	12:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	104	ph tos nsitiv .clm. and (black near (matrix	USPAT;	2003/01/27
		or matrices)).clm.	US-PGPUB;	12:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	87	(photosensitive.clm. and (black near (matrix	USPAT;	2003/01/27
•	0.	or matrices)).clm.) and (method or	US-PGPUB;	12:55
		process).clm.	EPO; JPO;	12.55
		process).cim.	DERWENT;	
			• 1	
	40	Makada a sasidina aku and Malada na sa	IBM_TDB	2002/04/27
	12	((photosensitive.clm. and (black near	USPAT;	2003/01/27
		(matrix or matrices)).clm.) and (method or	US-PGPUB;	12:56
		process).clm.) and (etch or etching or	EPO; JPO;	
		etched).clm.	DERWENT;	
			IBM_TDB	
-	11	(((photosensitive.clm. and (black near	USPAT;	2003/01/27
		(matrix or matrices)).clm.) and (method or	US-PGPUB;	12:57
		process).clm.) and (etch or etching or	EPO; JPO;	
		etched).clm.) and transparent	DERWENT;	
			IBM_TDB	
	4	((transparent near electrode) and (black	USPAT;	2003/01/27
		near (matrix or matrices)) and	US-PGPUB;	13:00
		(photosensitive or resin or epoxy) and (etch	EPO; JPO;	
		or etching or etched) and mask and (method	DERWENT;	
		or process)).clm.	IBM_TDB	
	10	((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matrices)) and (photosensitive or resin or	US-PGPUB;	13:01
		epoxy) and (etch or etching or etched) and	EPO; JPO;	13.01
			DERWENT;	
		mask and (method or process)).clm.	1	
	40		IBM_TDB	0000104107
•	10	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matrices)) and (photosensitive or resin or	US-PGPUB;	13:02
		epoxy) and (etch or etching or etched) and	EPO; JPO;	
		mask and (method or process)).clm.) and	DERWENT;	
		(mask or masking or masked)	IBM_TDB	
•	10	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
	ļ.	matrices)) and (photosensitive or resin or	US-PGPUB;	13:03
		epoxy) and (etch or etching or etched) and	EPO; JPO;	
		mask and (method or process)).clm.) and	DERWENT;	
		(mask or masking or masked).clm.	IBM_TDB	
	24	((black near (matrix or matrices)) and	USPAT;	2003/01/27
		(transparent same electrode same	US-PGPUB;	13:06
		substrat) and (mask or masking r masked)	EPO; JPO;	
		and (m th d or proc ss)).clm.	DERWENT;	

-	4	(((black near (matrix or matrices)) and	USPAT;	2003/01/27
Ì		(transpar nt same ctrode same	US-PGPUB;	13:07
		substrat) and (mask or masking r masked)	EPO; JPO;	
		and (m th d r process)).clm.) and	DERWENT;	
		(ph to\$15).clm.	IBM_TDB	
	18	(((black near (matrix or matrices)) and	USPAT:	2003/01/27
	10	((transparent same electrode same	US-PGPUB;	13:11
į	9 11	•		13.11
	1 11	substrate) and (mask or masking or masked)	EPO; JPO;	
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
	10	photo-sensitive or photo-resist or resin or		
		epoxy or resist).clm.		A
	13	((((black near (matrix or matrices)) and	USPAT;	2003/01/27
		(transparent same electrode same	US-PGPUB;	13:13
		substrate) and (mask or masking or masked)	EPO; JPO;	
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
		photo-sensitive or photo-resist or resin or	_	
		epoxy or resist).clm.) and (color near filter)		
	2	(((((black near (matrix or matrices)) and	USPAT;	2003/01/27
	-	(transparent same electrode same	US-PGPUB;	13:13
		substrate) and (mask or masking or masked)	EPO; JPO;	10110
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
		photo-sensitive or photo-resist or resin or		
		epoxy or resist).clm.) and (color near filter))		
	1	and chrome		
	8	(((((black near (matrix or matrices)) and	USPAT;	2003/01/27
		(transparent same electrode same	US-PGPUB;	13:20
+		substrate) and (mask or masking or masked)	EPO; JPO;	
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
		photo-sensitive or photo-resist or resin or	_	
		epoxy or resist).clm.) and (color near filter))		
		and ((black near (matrix or matrices))		
		near10 (resin or epoxy or photosensitive or		
		photo-sensitive or photoresist or resist or	1	
		photo-resist)).clm.		2002/04/07
	2	(substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate near line) and (data	US-PGPUB;	13:24
		near line) and (pixel same electrode) and	EPO; JPO;	
		redundant and (switch or switching or	DERWENT;	
		switched) and protrusion).ti,ab,clm.	IBM_TDB	
	2	(substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate near line) and (data	US-PGPUB;	13:26
		near line) and (pixel same electrode) and	EPO; JPO;	
		(redundant near data) and	DERWENT;	5
İ		1	IBM_TDB	
1	_	protrusi n).ti,ab,clm.		2003/01/27
	2	(substrat and (insulating or insulat r or	USPAT;	
		diel ctric) and (gat n ar lin) and (data	US-PGPUB;	13:28
		n ar lin) and pix I and (r dundant near	EPO; JPO;	
		data) and pr trusion).ti,ab,clm.	DERWENT;	
			IBM_TDB	

•	2	(substrat and (insulating rinsulat ror	USPAT;	2003/01/27
		diel ctric) and (gat) and (data) and pix I	US-P PUB;	13:30
		and (r dundant near data) and	EPO; JPO;	
		pr trusi n).ti,ab,clm.	DERWENT;	
			IBM_TDB	
	2	(substrate and (insulating rinsulat r r	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:30
		and (redundant) and protrusion).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	27	(substrate and (insulating or insulator or	USPAT:	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:32
		and protrusion).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	3	((substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:31
		and protrusion).ti,ab,clm.) and redundant	EPO; JPO;	
		, , , ,	DERWENT;	
			IBM_TDB	
•	4	(substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:33
		and protrusion and (redundant or	EPO; JPO;	
		repair)).ti,ab,clm.	DERWENT;	
	1	••••••	IBM_TDB	
_ 0	3	((substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:34
		and protrusion and (redundant or	EPO; JPO;	
		repair)).ti,ab,clm.) and (matrix or matrices)	DERWENT;	
		,	IBM_TDB	
_	2	(((substrate and (insulating or insulator or	USPAT;	2003/01/27
	.1	dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:33
		and protrusion and (redundant or	EPO; JPO;	
		repair)).ti,ab,clm.) and (matrix or matrices))	DERWENT;	
		and transparent	IBM_TDB	
-	1797	((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:37
		pixel)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	54	(((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:41
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
	l b	ner filter) and transparent and protrusion	DERWENT;	
			IBM_TDB	

	28	((((insulating or insulat r r dielectric) and	USPAT;	2003/01/27
		(gate n ar line) and (data near line) and	US-PGPUB;	13:48
		pixel)) and (matrix or matrices) and (col r	EPO; JPO;	
		n r filt r) and transpar nt and protrusi n)	DERWENT:	
		and (organic) and (photoresist r	IBM TDB	
		ph t -resist r ph t lithography or	_	
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)		
	25	(((((insulating or insulator or dielectric) and	USPAT:	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB:	13:52
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	15.52
		- 17	DERWENT;	
		ner filter) and transparent and protrusion)	IBM_TDB	
		and (organic) and (photoresist or	10111_100	
		photo-resist or photolithography or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter)		00000000000
	3	((((((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:56
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
		ner filter) and transparent and protrusion)	DERWENT;	
1		and (organic) and (photoresist or	IBM_TDB	
		photo-resist or photolithography or	1	
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter))		3
ŀ		and image and (scan or scannig) and		
		(transmit or transmitting or transmitted or		
		transmission) and (switch or switching or		
1		switched)		
	16	((((((insulating or insulator or dielectric) and	USPAT;	2003/01/27
1		(gate near line) and (data near line) and	US-PGPUB;	13:57
İ		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
		ner filter) and transparent and protrusion)	DERWENT;	
		and (organic) and (photoresist or	!BM_TDB	
		photo-resist or photolithography or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter))		
		and (black near (matrix or matrices))		

•	12	(((((((insulating or insulator or di lectric) and (gate near lin) and (data n ar line) and	USPAT; US-PGPUB;	2003/01/27 13:59
		pix I)) and (matrix r matric s) and (col r	EPO; JPO;	13.39
		ner filter) and transparent and pr trusi n)	DERWENT;	
		and (rganic) and (photoresist r	IBM_TDB	
		ph to-resist r ph t lith graphy or	10111_100	
		photo-lithography or photosensitive or		
		photo-innography or photosensitive or photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter))		
		and (black near (matrix or matrices))) and		
		image		
-	1	(((((((insulating or insulator or dielectric)	USPAT;	2003/01/27
		and (gate near line) and (data near line) and	US-PGPUB;	13:59
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
		ner filter) and transparent and protrusion)	DERWENT;	
		and (organic) and (photoresist or	IBM_TDB	
		photo-resist or photolithography or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter))		•
		and (black near (matrix or matrices))) and		
		image) and (redundant or repair)		
•	72	((redundant or repair) and gate and data and	USPAT;	2003/01/27
		pixel and (insulating or insulator or	US-PGPUB;	14:03
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.	DERWENT;	
			IBM_TDB	
•	33	(((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:04
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
	1	(gate near line)		
-	1	((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:05
	B	dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
	1	near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and (organic near black		
		near (matrix or matrices))	(
-	1	((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:10
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and (rganic sam (black		
		near (matrix r matrices)))		

-	5	((((r dundant or repair) and gate and data	USPAT;	2003/01/27
	İ	and pixel and (insulating or insulator or	US-PGPUB;	14:14
		dielectric) and (Icd or liquid-crystal r (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data n ar lin) and	IBM_TDB	
		(gate near line)) and ((black near (matrix or		
		matrices)))		
	2	(((((redundant or repair) and gate and data	USPAT;	2003/01/27
	-	and pixel and (insulating or insulator or	US-PGPUB:	14:20
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	14120
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
			-	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and ((black near (matrix or		
		matrices)))) and organic		2002/04/07
	20	((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:28
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic		
	18	(((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:29
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	1
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic) and (pixel	_	
		same electrode) and (aperture or whole or		
		opening or gap or window)		
1	18	(((((redundant or repair) and gate and data	USPAT;	2003/01/27
	18		US-PGPUB;	14:30
		and pixel and (insulating or insulator or		17.30
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic) and (pixel		
		near5 electrode) and (aperture or whole or		
		opening or gap or window)		
	8	((((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:31
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic) and (pixel		
		near5 electrode) and (aperture or whole or		
		opening or gap or window)) and molecule		
	_	, , ,	USPAT;	2003/01/27
	5	(((((((redundant or repair) and gate and data	1	14:31
		and pixel and (insulating or insulator or	US-PGPUB;	14:31
1		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		n ar crystal) r display)).ti,ab,clm.) and	DERWENT;	
		(pix I and image) and (data n ar lin) and	IBM_TDB	
		(gat n ar lin)) and rganic) and (pix l		
		near5 ctr de) and (aperture r wh r		
		p ning rgap rwindow)) and m l cul)		
		and angle		

-	5	((((((((redundant or repair) and gate and data and pix I and (insulating or insulator r	USPAT; US-PGPUB;	2003/01/27 14:32
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		n ar crystal) r display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gat near lin)) and rganic) and (pixel		
		near5 electrode) and (aperture or whole or opening or gap or window)) and molecule)		
		and angle) and (scan or scanning or		
		scanned)		
i .	5	(((((((((redundant or repair) and gate and	USPAT:	2003/01/27
	_	data and pixel and (insulating or insulator or	US-PGPUB;	14:41
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic) and (pixel		
		near5 electrode) and (aperture or whole or		
		opening or gap or window)) and molecule)		
		and angle) and (scan or scanning or		
		scanned)) and (transmission or transmit or		
		transmitting or transmitted)		0000/04/07
-	36	((insulating or insulator or dielectric) same	USPAT;	2003/01/27 14:45
		substrate same transparent same electrode	US-PGPUB; EPO; JPO;	14:45
		same (light-blocking or (light near (block or	DERWENT;	
		blocking or blocked)) same metal same protrusion))	IBM TDB	
	1	(((insulating or insulator or dielectric) same	USPAT;	2003/01/27
-	•	substrate same transparent same electrode	US-PGPUB;	14:46
		same (light-blocking or (light near (block or	EPO; JPO;	
		blocking or blocked)) same metal same	DERWENT;	
		protrusion)).ti,ab,clm.) and organic	IBM_TDB	
-	5	((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate same transparent same electrode	US-PGPUB;	14:46
		same (light-blocking or (light near (block or	EPO; JPO;	
		blocking or blocked)) same metal same	DERWENT;	
		protrusion)).ti,ab,clm.	IBM_TDB	
-	6	((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate same transparent same electrode	US-PGPUB;	14:48
		same (light-blocking or (light near (block or	EPO; JPO;	
		blocking or blocked)) same metal same	DERWENT;	
		protrusion)) and organic	IBM_TDB	2003/01/27
-	3	(((insulating or insulator or dielectric) same	USPAT;	14:49
		substrate same transparent same electrode	US-PGPUB; EPO; JPO;	14:43
	1	same (light-blocking or (light near (block or blocking or blocked)) same metal same	DERWENT;	
		protrusion)) and organic) and (pixel near	IBM_TDB	
		electrode)	10 100	
	4	(((insulating rinsulat rordi l ctric) sam	USPAT;	2003/01/27
	-	substrat sam transpar nt same I ctr d	US-PGPUB;	15:05
		sam (light-blocking r (light n ar (bl ck r	EPO; JPO;	
		blocking or bl ck d)) sam m tal sam	DERWENT;	
		pr trusi n)) and rganic) and (pix l)	IBM_TDB	

 3	(((insulating or insulat r or di l ctric) same	USPAT;	2003/01/27
	substrate same transparent sam ctrode	US-PGPUB;	14:50
	same (light-blocking r (light n ar (bl ck r bl cking r bl cked)) sam m tal sam	EPO; JPO; DERWENT;	
	pr trusion)) and organic) and	IBM_TDB	
	(pixel).ti,ab,clm.		
3	((((insulating or insulator or dielectric) same	USPAT;	2003/01/27
	substrate same transparent same electrode	US-PGPUB;	14:53
•	same (light-blocking or (light near (block or	EPO; JPO;	
	blocking or blocked)) same metal same	DERWENT;	
	protrusion)) and organic) and (pixel)) and	IBM_TDB	
	(thin near5 transistor)		1